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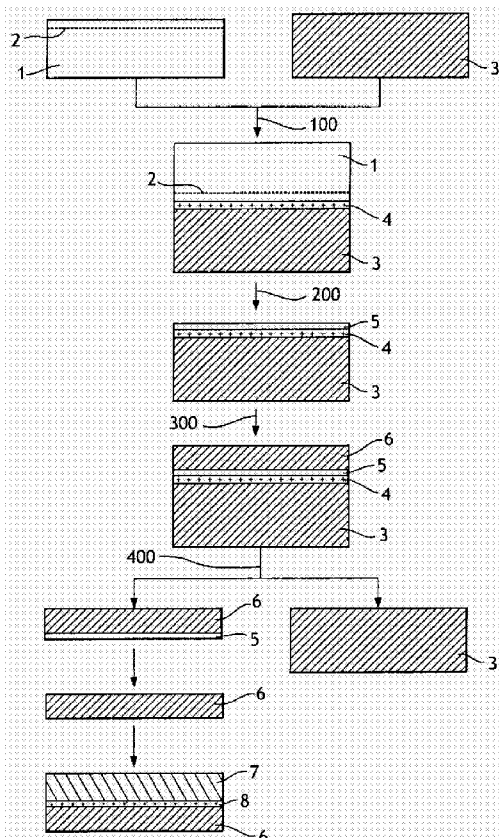
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(54) Title: METHOD FOR THE MANUFACTURE OF SUBSTRATES, IN PARTICULAR FOR THE OPTICAL, ELECTRONIC OR OPTOELECTRONIC AREAS, AND THE SUBSTRATE OBTAINED IN ACCORDANCE WITH THE SAID METHOD



(57) Abstract: A method for the manufacture of substrates, in particular for the optical, electronic or optoelectronic areas, and a substrate created in accordance with the said method. This present invention concerns a method for the manufacture of substrates, in particular for the optical, electronic or optoelectronic areas, that includes at least the following stages for the transfer of a seed layer (5) onto a receiving support (3), and the epitaxy of a usable layer (6) onto the seed layer (5), the said method being notable in that the thermal coefficient of expansion of the receiving support (3) is identical to or slightly greater than the thermal coefficient of expansion of the usable layer (6), and the thermal coefficient of expansion of the seed layer (5) is more-or-less equal to the thermal coefficient of expansion of the receiving support (3).

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